

## **Features**

- Split Gate Trench MOSFET Technology
- Excellent Package for Heat Dissipation
- Halogen Free. "Green" Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)
- Moisture Sensitivity Level 1

## **Maximum Ratings**

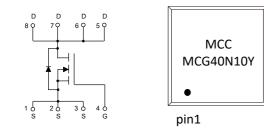
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 25°C/W Junction to Ambient(t≤10s)<sup>(2)</sup>
- Thermal Resistance: 55°C/W Junction to Ambient(Steady-State)<sup>(2)</sup>
- Thermal Resistance: 2.9°C/W Junction to Case(Steady-State)

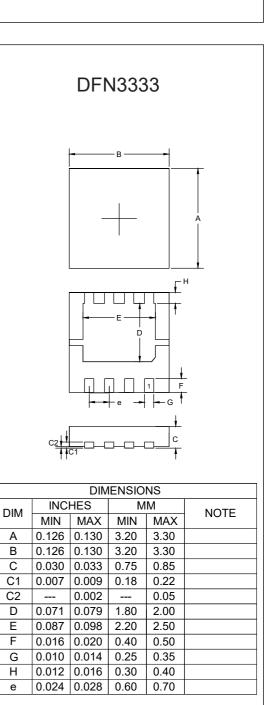
| Parameter                                     | Symbol          | Rating | Unit |
|---|-----------------|--------|------|
| Drain-Source Voltage                          | V <sub>DS</sub> | 100    | V    |
| Gate-Source Volltage                          | V <sub>GS</sub> | ±20    | V    |
| Continuous Drain Current                      | I <sub>D</sub>  | 40     | Α    |
| Pulsed Drain Current <sup>(3)</sup>           | I <sub>DM</sub> | 160    | Α    |
| Total Power Dissipation <sup>(4)</sup>        | P <sub>D</sub>  | 43     | W    |
| Single Pulsed Avalanche Energy <sup>(5)</sup> | E <sub>AS</sub> | 81     | mJ   |

Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of R<sub>0JA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub> =25°C. The Power dissipation P<sub>DSM</sub> is based on R<sub>0JA</sub> t ≤ 10s and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Repetitive rating; pulse width limited by max. junction temperature.
- 4.  $P_D$  is based on max. junction temperature, using junction-case thermal resistance.
- 5.  $T_J$ =25°C,  $V_{DD}$ =50V,  $R_G$ =25 $\Omega$ , L=0.5mH.

## Internal Structure and Marking Code





**N-CHANNEL** 

MOSFET

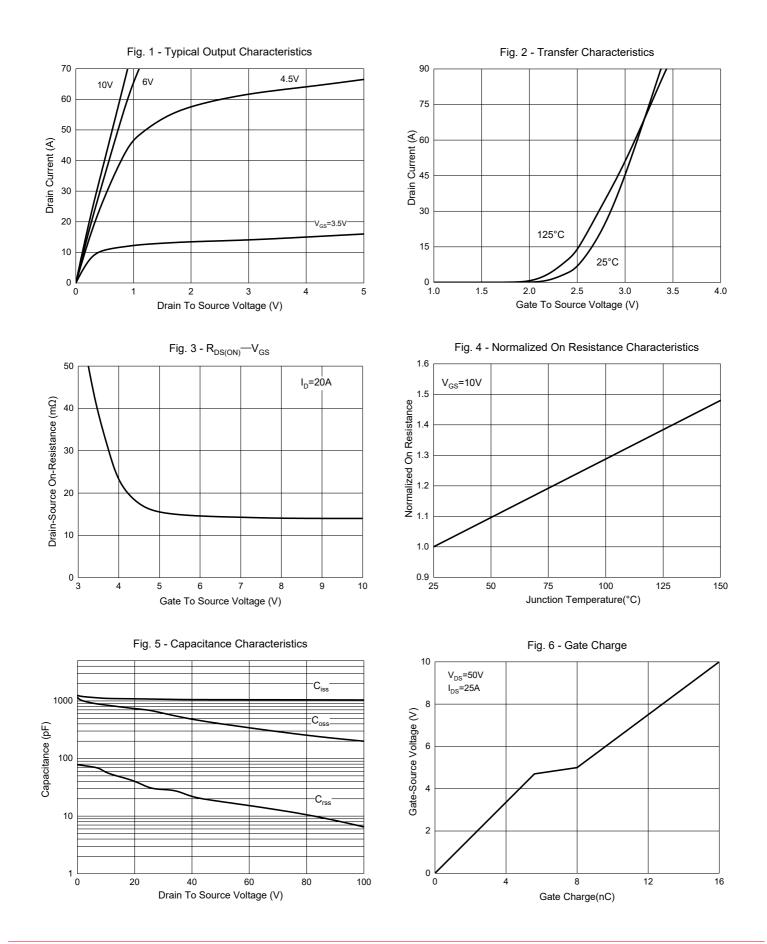


## Electrical Characteristics @ 25°C (Unless Otherwise Specified)

| Parameter                       | Symbol               | Test Conditions   | Min | Тур  | Max  | Unit |  |
|---------------------------------|----------------------|---|-----|------|------|------|--|
| Static Characteristics          | 1                    |   |     | 1    | 1    | L    |  |
| Drain-Source Breakdown Voltage  | V <sub>(BR)DSS</sub> | V <sub>GS</sub> =0V, I <sub>D</sub> =250µA                    | 100 |      |      | V    |  |
| Gate-Source Leakage Current     | I <sub>GSS</sub>     | V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V                    |     |      | ±100 | nA   |  |
| Zero Gate Voltage Drain Current | I <sub>DSS</sub>     | V <sub>DS</sub> =100V, V <sub>GS</sub> =0V                    |     |      | 1    | μA   |  |
| Gate-Threshold Voltage          | V <sub>GS(th)</sub>  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250µA      | 1   | 1.8  | 2.5  | V    |  |
| Drain-Source On-Resistance      |                      | V <sub>GS</sub> =10V, I <sub>D</sub> =20A                     |     | 15   | 18.5 | mΩ   |  |
|                                 | R <sub>DS(on)</sub>  | V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A                    |     | 18   | 22.5 | mΩ   |  |
| Gate Resistance                 | R <sub>g</sub>       | F=1 MHz, Open drain   |     | 1    |      | Ω    |  |
| Diode Characteristics           |                      |   | 1   |      |      |      |  |
| Continuous Body Diode Current   | I <sub>S</sub>       |   |     |      | 40   | А    |  |
| Diode Forward Voltage           | V <sub>SD</sub>      | V <sub>GS</sub> =0V, I <sub>S</sub> =20A                      |     |      | 1.3  | V    |  |
| Reverse Recovery Time           | t <sub>rr</sub>      |   |     | 39.8 |      | ns   |  |
| Reverse Recovery Charge         | Q <sub>rr</sub>      | l <sub>F</sub> =20A, dl <sub>F</sub> /dt=100A/µs              |     | 42   |      | nC   |  |
| Dynamic Characteristics         |                      |   |     |      |      |      |  |
| Input Capacitance               | C <sub>iss</sub>     | V <sub>DS</sub> =50V,V <sub>GS</sub> =0V,f=1MHz               |     | 1051 |      |      |  |
| Output Capacitance              | C <sub>oss</sub>     |   |     | 399  |      | pF   |  |
| Reverse Transfer Capacitance    | C <sub>rss</sub>     |   |     | 18   |      | 1    |  |
| Total Gate Charge               | Qg                   | V <sub>DS</sub> =50V,V <sub>GS</sub> =10V,I <sub>D</sub> =25A |     | 16   |      |      |  |
| Gate-Source Charge              | Q <sub>gs</sub>      |   |     | 5.6  |      | nC   |  |
| Gate-Drain Charge               | Q <sub>gd</sub>      |   |     | 2.4  |      | -    |  |
| Turn-On Delay Time              | t <sub>d(on)</sub>   |   |     | 39.2 |      |      |  |
| Turn-On Rise Time               | t <sub>r</sub>       | V <sub>DS</sub> =50V, V <sub>GS</sub> =10V,                   |     | 11   |      |      |  |
| Turn-Off Delay Time             | t <sub>d(off)</sub>  | R <sub>G</sub> =2.2Ω, I <sub>DS</sub> =25A                    |     | 53.2 |      | ns   |  |
| Turn-Off Fall Time              | t <sub>f</sub>       |   |     | 15.8 |      |      |  |



# **Curve Characteristics**





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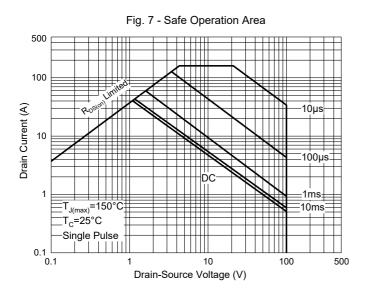
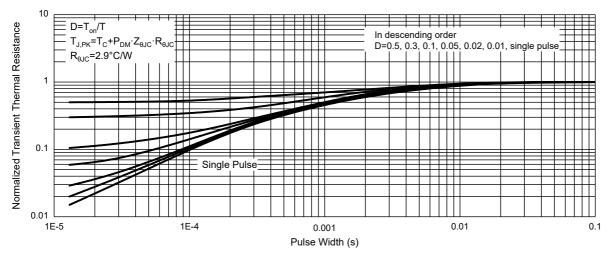


Fig. 8 - Normalized Transient Thermal Impedance





| Device         | Packing               |  |
|----------------|-----------------------|--|
| Part Number-TP | Tape&Reel: 5Kpcs/Reel |  |

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